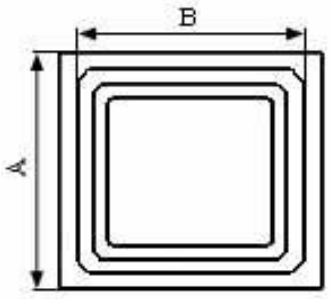
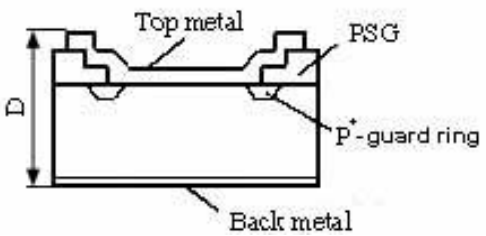
mikron VSP-MIKRON

	15A/40V. Die Size-123mil. RoHS			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	15,0	-
DC Forward Voltage @ 25˚C, I_F=15,0A	V_F	V	0,51	0,49
Maximum Reverse Current @ 25˚C, V_R=45V @ 25˚C, V_R=40V @ 125˚C, V_R=40V	I_R	mA	- 0,150 75,0	0,150 0,100 70,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	250	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<150˚C.	I_{RRM}	A	4,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	150	





DIM	ITEM	µm
A_X A_y	Wafer Form Die Size	3120 3120
B_X B_y	Top Metal Size	2980 2980
D	Thickness	300max.
Scribe line Width		80

Top metal:
a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.